



STPS61170C

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

Table 1: Main Product Characteristics

$I_{F(AV)}$	2 x 30 A
V_{RRM}	170 V
T_j	175 °C
$V_F(max)$	0.67 V

FEATURES AND BENEFITS

- High junction temperature capability
- Low leakage current
- Good trade off between leakage current and forward voltage drop
- Low thermal resistance
- High frequency operation
- Avalanche specification

DESCRIPTION

Dual center tab Schottky rectifier suited for High Frequency Switch Mode Power Supply. Packaged in TO-247, this device is intended for use to enhance the reliability of the application.

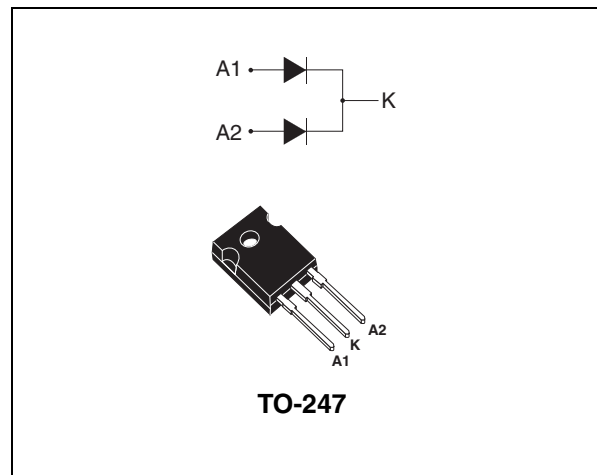


Table 2: Order Code

Part Number	Marking
STPS61170CW	STPS61170CW

Table 3: Absolute Ratings (limiting values, per diode)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			170	V
$I_{F(RMS)}$	RMS forward current			80	A
$I_{F(AV)}$	Average forward current	$T_c = 150\text{ °C}$ $\delta = 0.5$	Per diode Per device	30 60	A
I_{FSM}	Surge non repetitive forward current		$t_p = 10\text{ ms sinusoidal}$	500	A
P_{ARM}	Repetitive peak avalanche power		$t_p = 1\text{ }\mu\text{s}$ $T_j = 25\text{ °C}$	31800	W
T_{stg}	Storage temperature range			-65 to + 175	°C
T_j	Maximum operating junction temperature *			175	°C
dV/dt	Critical rate of rise of reverse voltage			10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} > \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

Table 4: Thermal Parameters

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	0.9	$^{\circ}\text{C/W}$
		Total	0.6	
$R_{th(c)}$	Coupling		0.3	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

Table 5: Static Electrical Characteristics (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			60	μA
		$T_j = 125^{\circ}\text{C}$			16	60	mA
V_F^{**}	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 30\text{ A}$			0.84	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 30\text{ A}$		0.63	0.67	
		$T_j = 25^{\circ}\text{C}$	$I_F = 60\text{ A}$			0.92	
		$T_j = 125^{\circ}\text{C}$	$I_F = 60\text{ A}$		0.76	0.80	

Pulse test: * $t_p = 5\text{ ms}$, $\delta < 2\%$

** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation: $P = 0.54 \times I_{F(AV)} + 0.0043 I_F^2(\text{RMS})$

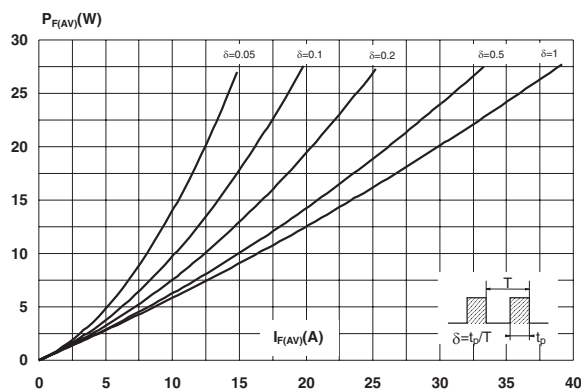
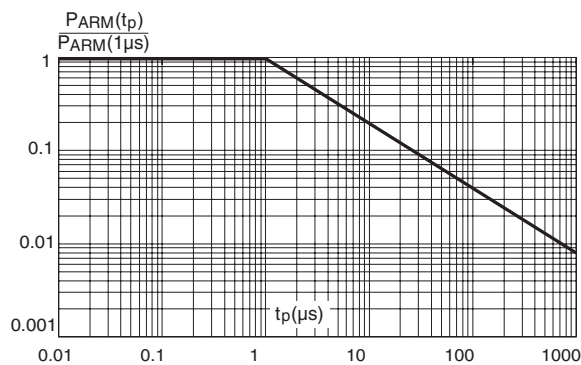
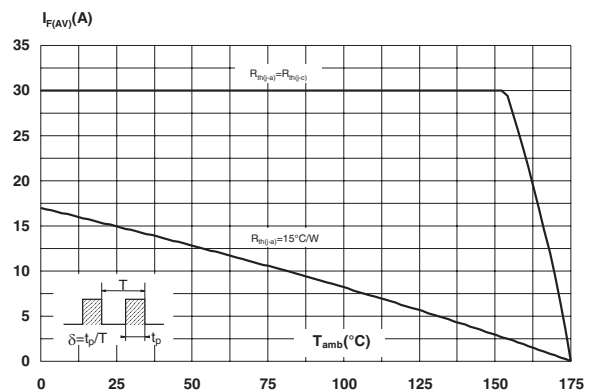
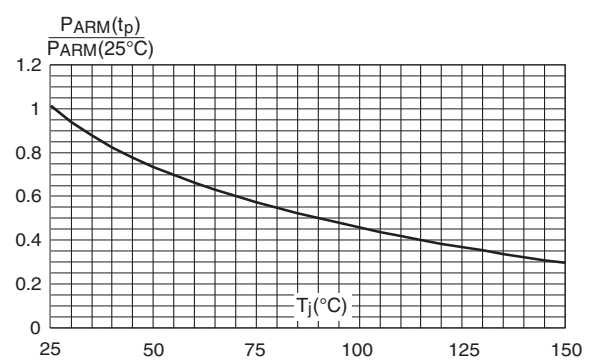
Figure 1: Average forward power dissipation versus average forward current (per diode)**Figure 3: Normalized avalanche power derating versus pulse duration****Figure 2: Average forward current versus ambient temperature ($\delta = 0.5$, per diode)****Figure 4: Normalized avalanche power derating versus junction temperature**

Figure 5: Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

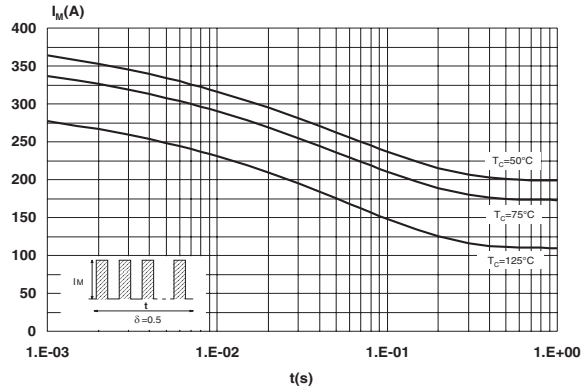


Figure 6: Relative variation of thermal impedance junction to case versus pulse duration (per diode)

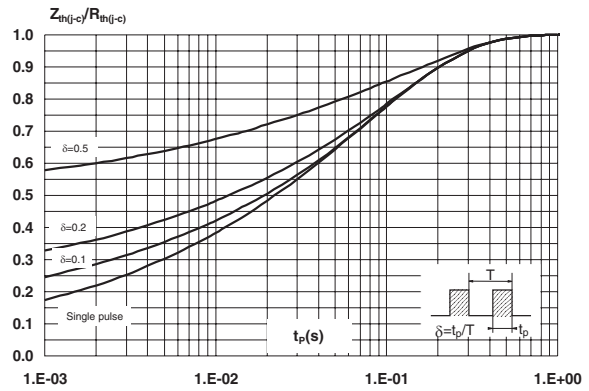


Figure 7: Reverse leakage current versus reverse voltage applied (typical values, per diode)

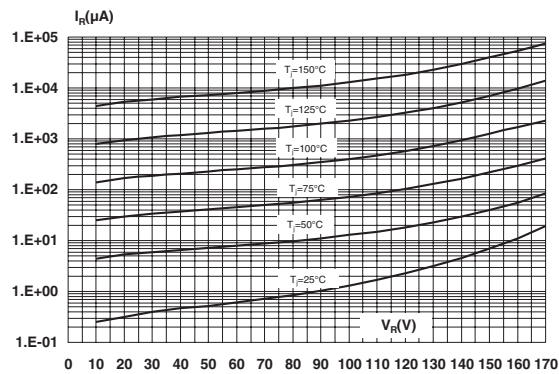


Figure 8: Junction capacitance versus reverse voltage applied (typical values, per diode)

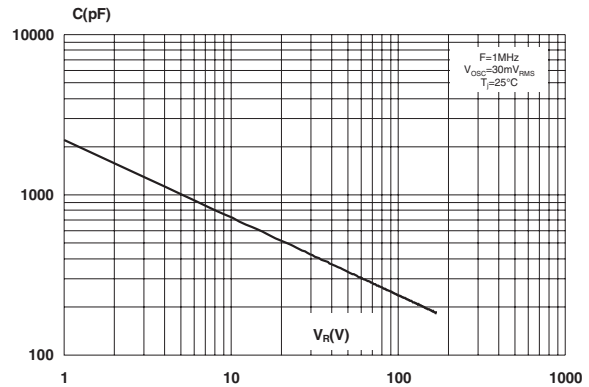


Figure 9: Forward voltage drop versus forward current (per diode, low level)

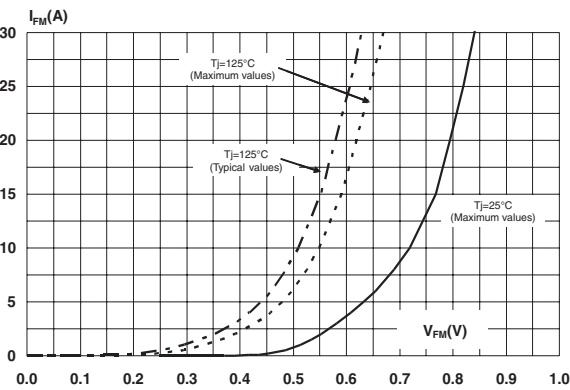


Figure 10: Forward voltage drop versus forward current (per diode, high level)

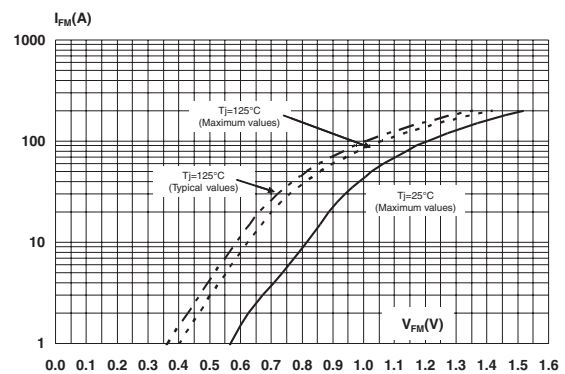


Figure 11: TO-247 Package Mechanical Data

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191		0.203
D	2.20		2.60	0.086		0.102
E	0.40		0.80	0.015		0.031
F	1.00		1.40	0.039		0.055
F1		3.00			0.118	
F2		2.00			0.078	
F3	2.00		2.40	0.078		0.094
F4	3.00		3.40	0.118		0.133
G		10.90			0.429	
H	15.45		15.75	0.608		0.620
L	19.85		20.15	0.781		0.793
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
L3	14.20		14.80	0.559		0.582
L4		34.60			1.362	
L5		5.50			0.216	
M	2.00		3.00	0.078		0.118
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139		0.143

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Table 6: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS61170CW	STPS61170CW	TO-247	4.40 g	30	Tube

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.8 Nm.
- Maximum torque value: 1.0 Nm.

Table 7: Revision History

Date	Revision	Description of Changes
16-Sep-2005	1	First issue.

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